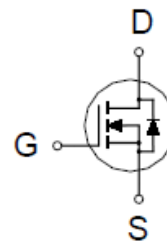
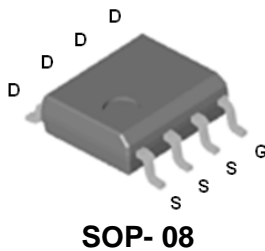


P1503BVG

N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	15m Ω @ $V_{GS} = 10V$	10A



100% Rg tested
100% UIS tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	I_D	10	A
	$T_A = 70\text{ }^\circ\text{C}$		8	
Pulsed Drain Current ¹		I_{DM}	40	
Avalanche Current		I_{AS}	10	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	5	mJ
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	2.5	W
	$T_A = 70\text{ }^\circ\text{C}$		1.6	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Lead	$R_{\theta JL}$		20	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		50	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

P1503BVG

N-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.5	3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 55 °C			10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	70			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 10A		17.5	24.0	mΩ
		V _{GS} = 10V, I _D = 10A		12.5	15.0	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 10A		18		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		699		pF
Output Capacitance	C _{oss}			229		
Reverse Transfer Capacitance	C _{rss}			143		
Total Gate Charge ²	Q _{g(VGS=10V)}	V _{DS} = 0.5V _{(BR)DSS} , I _D = 10A		18.4		nC
	Q _{g(VGS=4.5V)}			9.1		
Gate-Source Charge ²	Q _{gs}			2.6		
Gate-Drain Charge ²	Q _{gd}			4.8		
Turn-On Delay Time ²	t _{d(on)}		V _{DS} = 15V, I _D ≅ 1A, V _{GS} = 10V, R _{GEN} = 3Ω		5.5	
Rise Time ²	t _r			6.5		
Turn-Off Delay Time ²	t _{d(off)}			20		
Fall Time ²	t _f			5		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I _S				4.5	A
Pulsed Current ³	I _{SM}				9	
Forward Voltage ¹	V _{SD}	I _F = 10A, V _{GS} = 0V			1.1	V
Reverse Recovery Time	t _{rr}	I _F = 4.5A, dI _F /dt = 100A / μS		20	25	nS

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

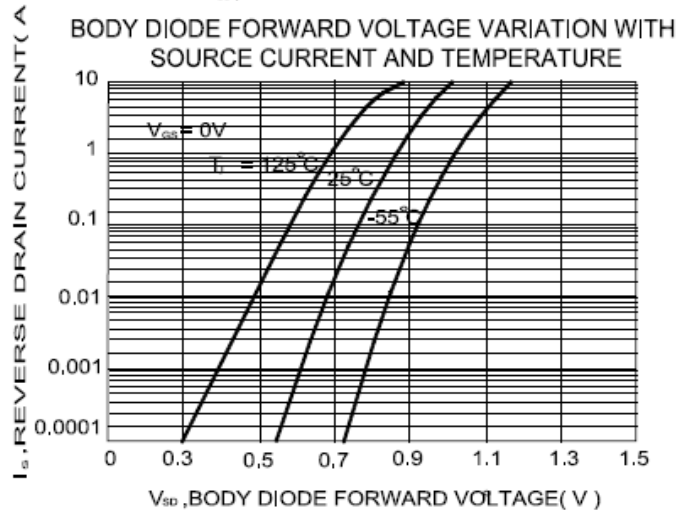
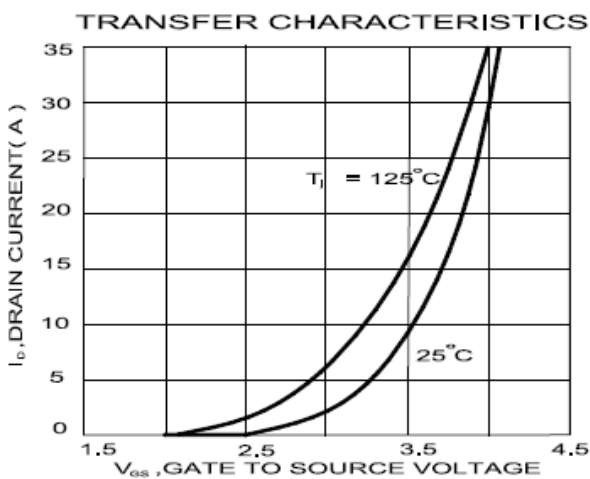
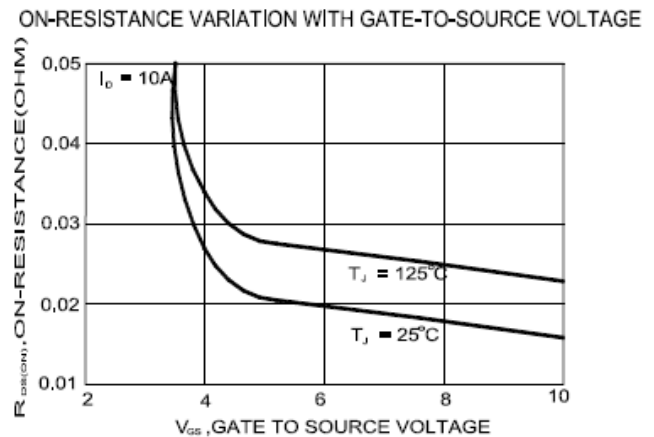
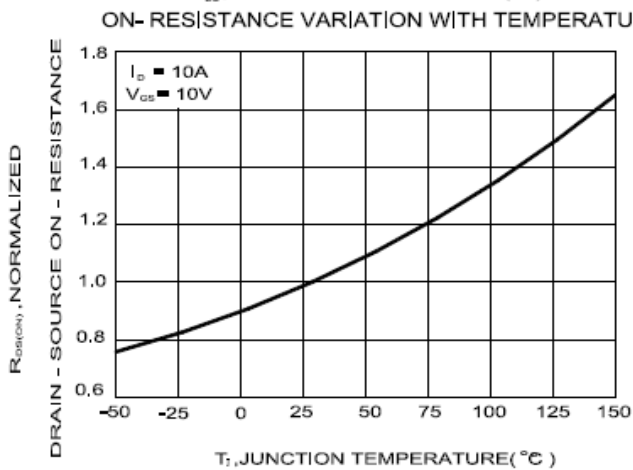
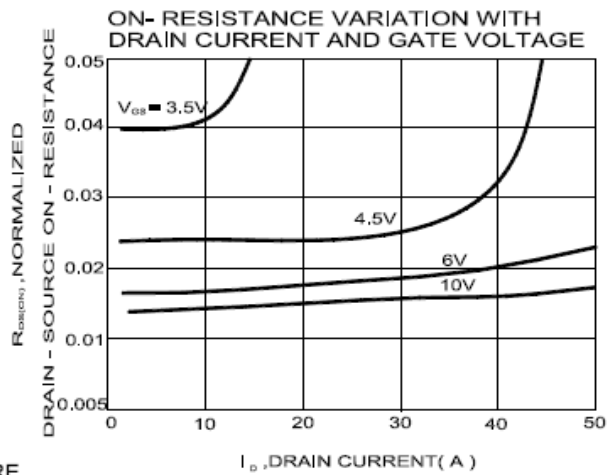
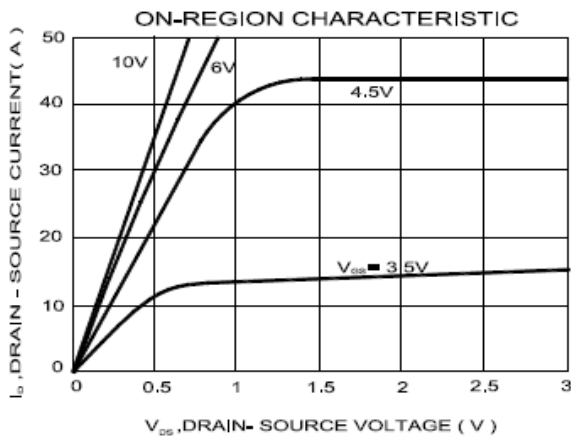
²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

P1503BVG

N-Channel Enhancement Mode MOSFET

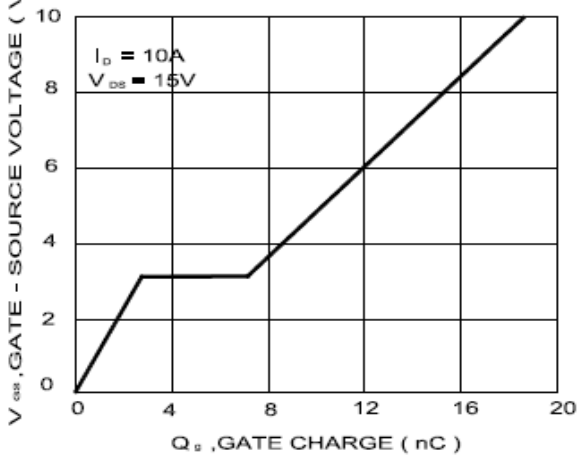
TYPICAL PERFORMANCE CHARACTERISTICS



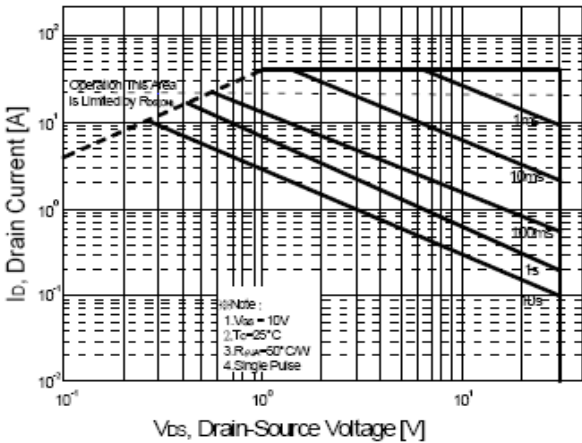
P1503BVG

N-Channel Enhancement Mode MOSFET

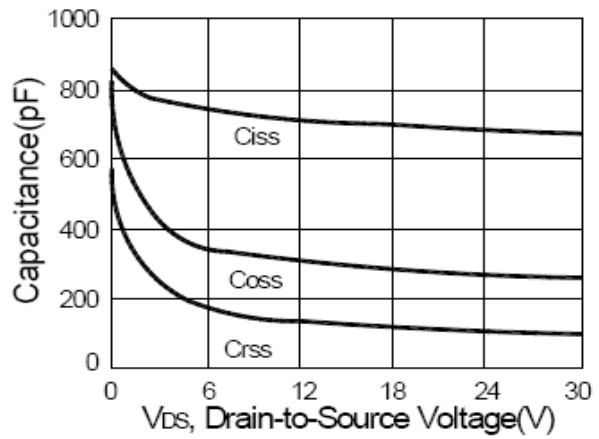
GATE CHARGE CHARACTERISTICS



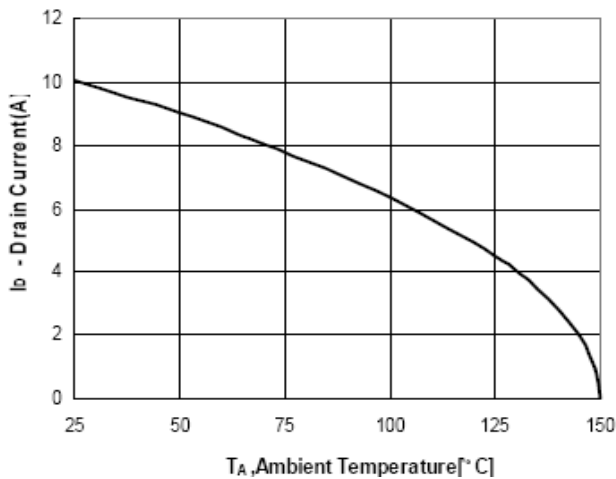
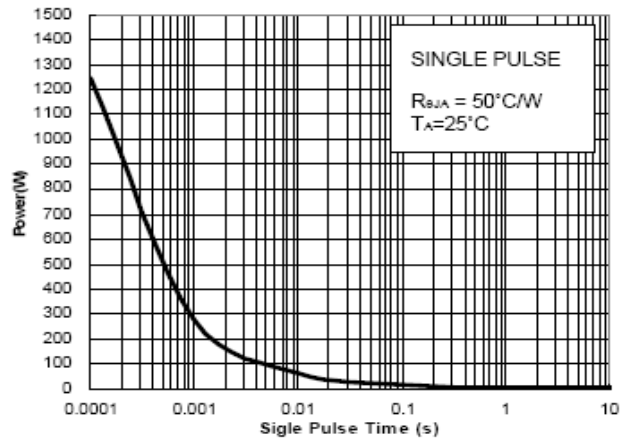
Maximum Safe Operating Area



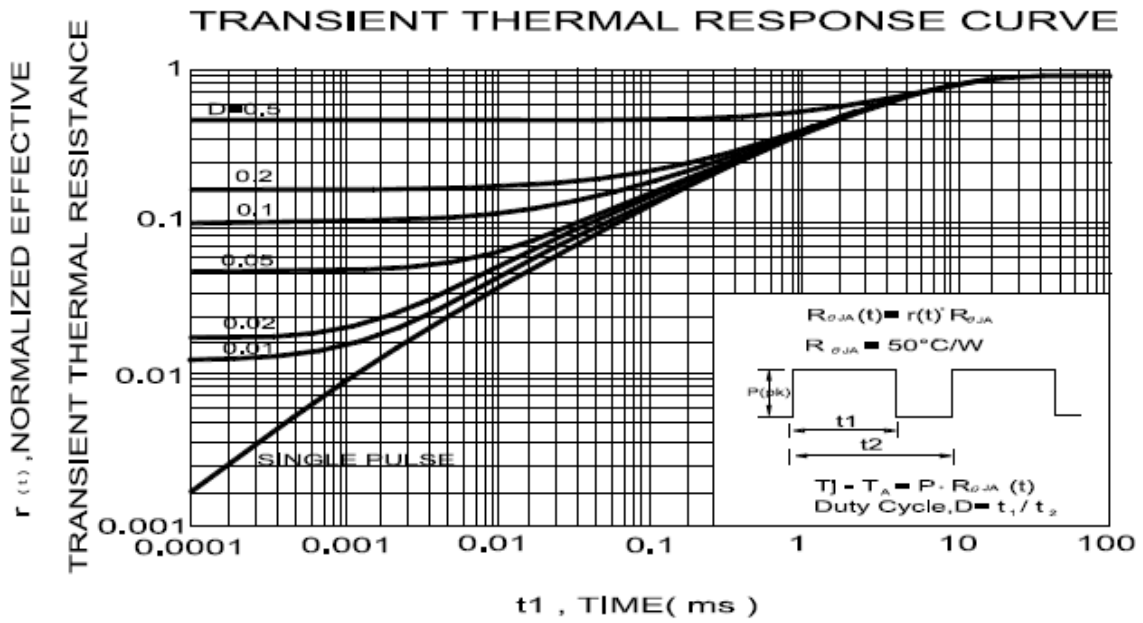
CAPACITANCE CHARACTERISTICS



Single Pulse Maximum Power Dissipation



P1503BVG
N-Channel Enhancement Mode MOSFET



P1503BVG

N-Channel Enhancement Mode MOSFET

Package Dimension

SOP-8 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.6	0.93
B	3.8	3.9	4.0	I	0.19	0.21	0.25
C	5.79	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.4	0.51	K	0°	3°	18°
E	1.25	1.27	1.29				
F	1.1	1.3	1.65				
G	0.05	0.15	0.25				

